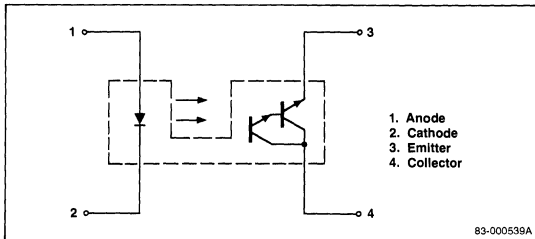


Description

The PS4001, PS4003, PS4005, PS4007, and PS4009 are photo coupled interrupter modules containing a GaAs light emitting diode and an NPN silicon Darlington connected photo transistor.

Pin Connection



Absolute Maximum Ratings

$T_A = +25^\circ\text{C}$

Diode	
Reverse Voltage, V_R	5.0V
Forward Current, I_F	50mA
Power Dissipation, P_D	100mW
Transistor	
Collector to Emitter Voltage, V_{CE0}	30V
Collector Current, I_C	50mA
Power Dissipation, P_D	100mW
Storage Temperature, T_{STG}	-40°C to $+100^\circ\text{C}$
Operating Temperature, T_{OPT}	-20°C to $+80^\circ\text{C}$

Electrical Characteristics

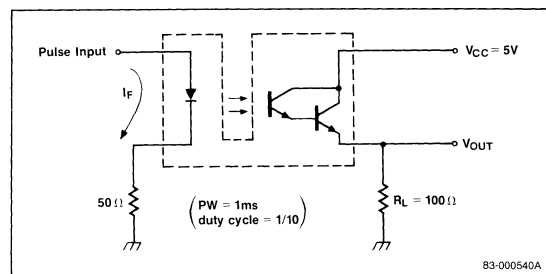
$T_A = +25^\circ\text{C}$

Parameter	Symbol	Limits			Unit	Test Conditions
		Min	Typ	Max		
Diode						
Forward Voltage	V_F	1.1	1.4		V	$I_F = 20\text{mA}$
Reverse Current	I_R		20		μA	$V_R = 4.0\text{V}$
Junction Capacitance	C	100			pF	$V = 0$, $f = 1.0\text{MHz}$
Transistor						
Collector to Emitter Dark Current	I_{CEO}		400		nA	$V_{CE} = 10\text{V}$, $I_F = 0$
Coupled						
Current Transfer Ratio	CTR (I_C/I_F)	20 ¹			%	$I_F = 10\text{mA}$, $V_{CE} = 2.0\text{V}$
Collector Saturation Voltage	$V_{CE(sat)}$		1.2		V	$I_F = 10\text{mA}$, $I_C = 0.5\text{mA}$
Rise Time	t_r		200		μs	$V_{CC} = 5.0\text{V}$, $I_C = 2.0\text{mA}$, $R_L = 100\Omega^2$
Fall Time	t_f		200		μs	$V_{CC} = 5.0\text{V}$, $I_C = 2.0\text{mA}$, $R_L = 100\Omega^2$

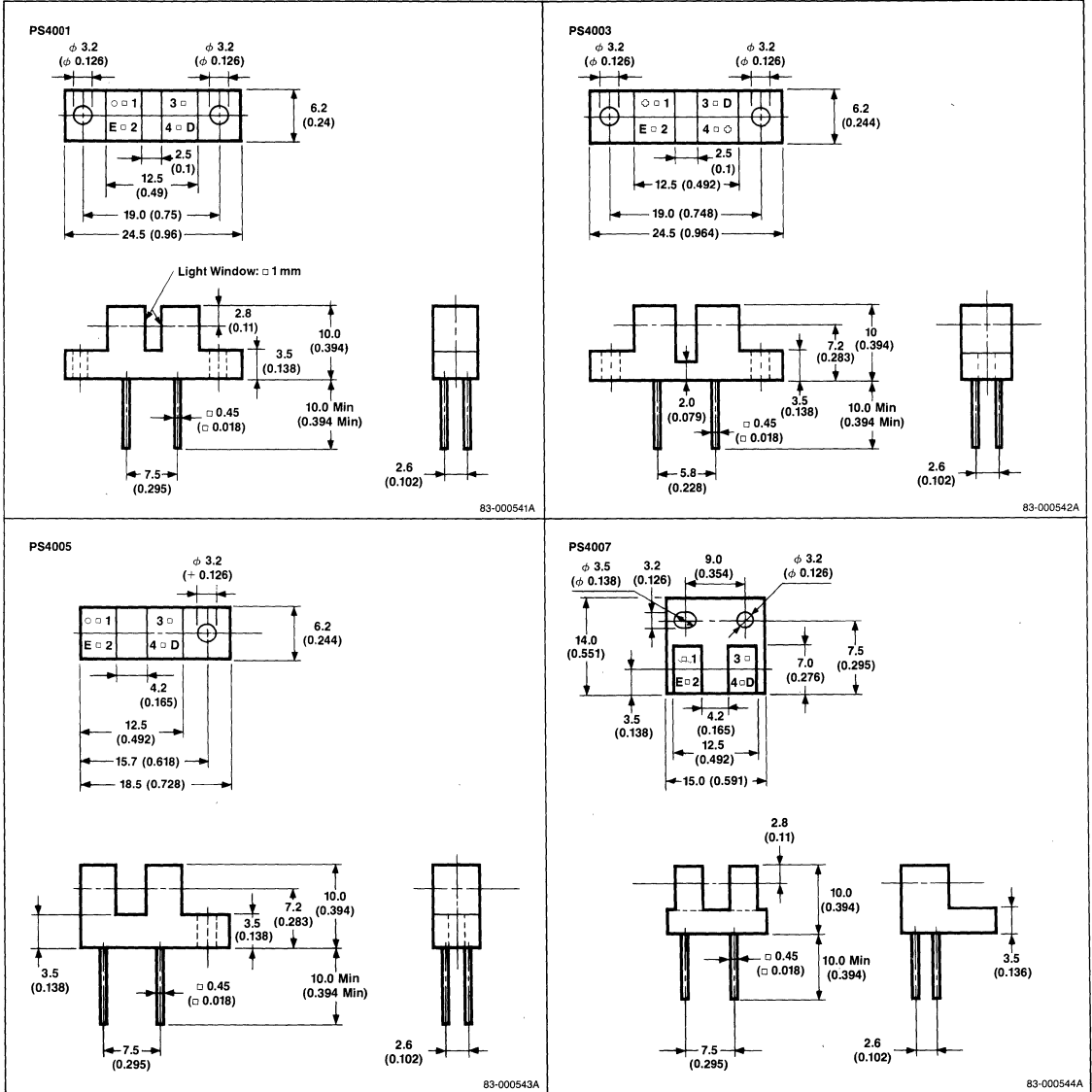
Notes: 1. PS4003: 15% min., others: 20% min.

2. Test circuit for switching time.

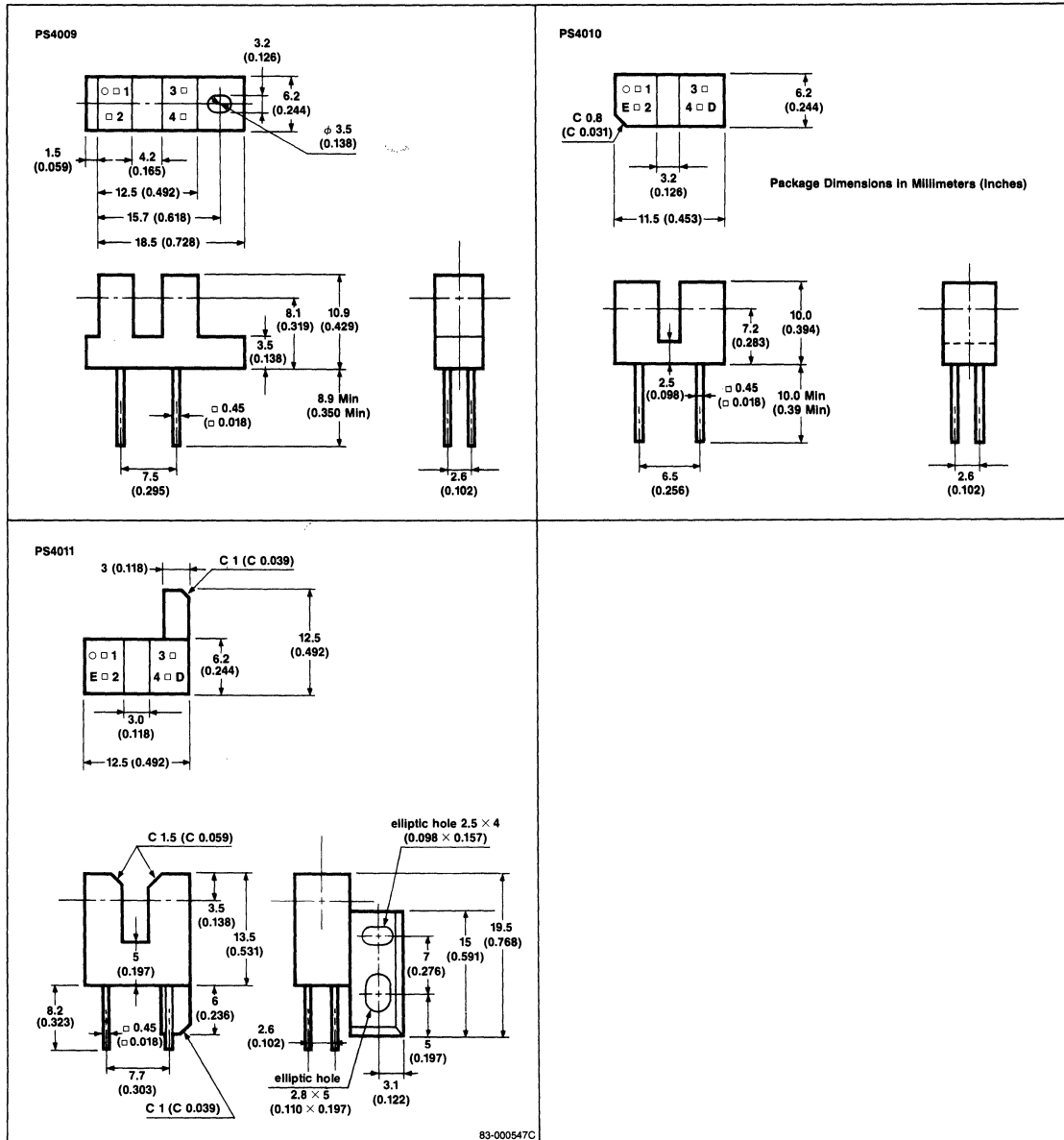
Test circuit for switching time



Package Dimensions

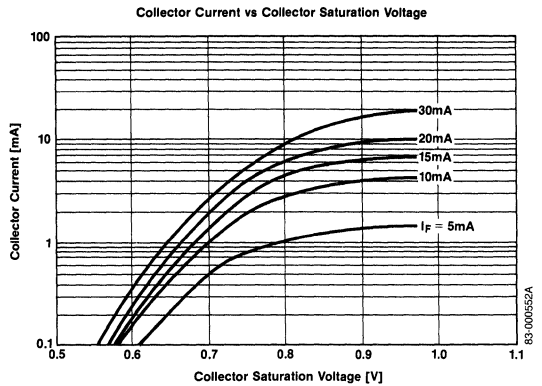
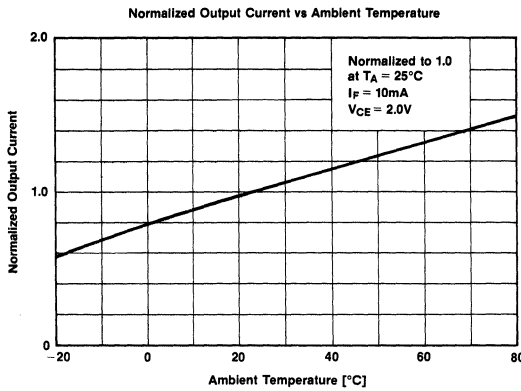
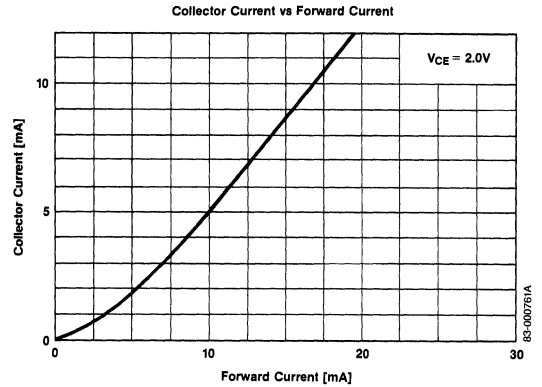
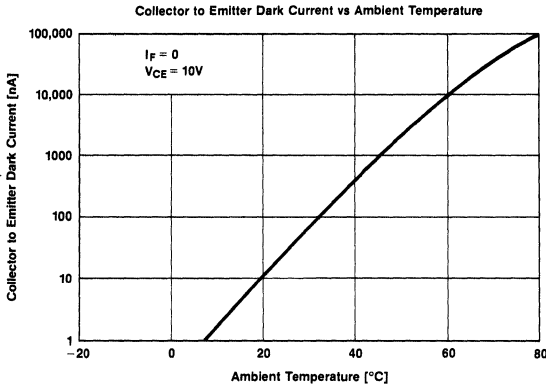
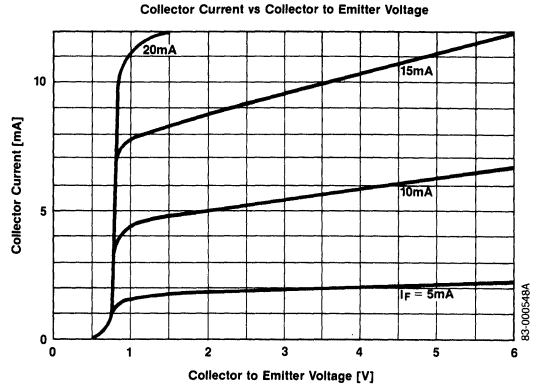
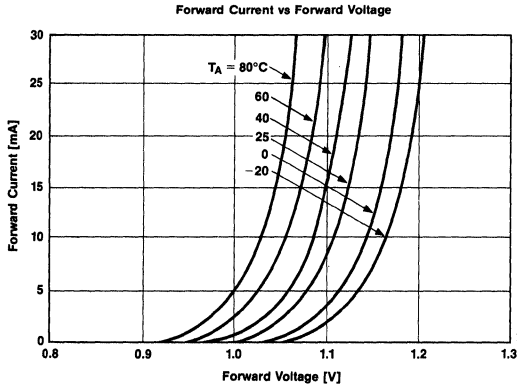


Package Dimensions (cont)



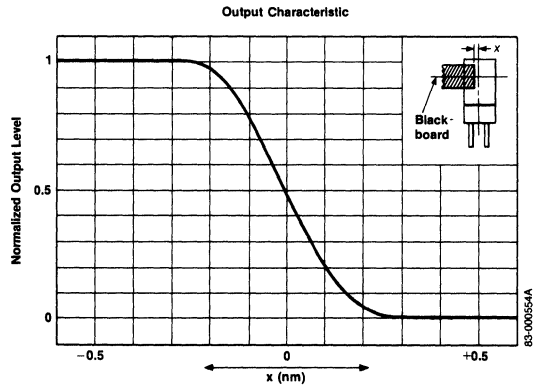
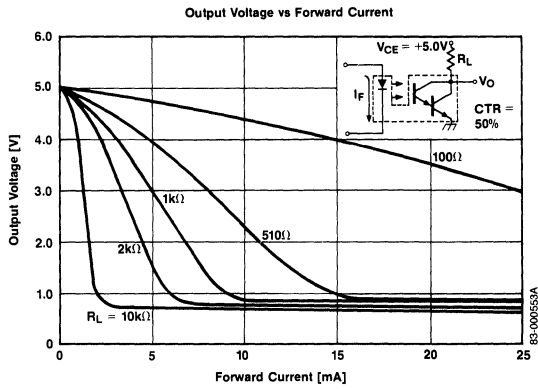
Typical Characteristics

$T_A = +25^\circ\text{C}$



Typical Characteristics (cont)

$T_A = +25^\circ\text{C}$



Typical Applications

